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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電 気 的 特 性 (T _b =25°C)										外 形	備 考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αb} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考			
				V _{CB0} (V)	V _{EBO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はパルス h _{FE}			バイアス		h _{FE}	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μΩ)			f _{βh} f _T * (Mc)	C _{ob} (pF)	r _{bb} h _{ie(renl)} * (Ω)
									(μA)	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CE} (V)	I _E (mA)	h _{FE}									
2SC2472	日立	RF.LN	Si.E	30	3	50	300	125	0.5	24	>20	10	5	10	-5	G _{re} > 13dB, N _F < 5 dB (V _{CE} =10V, I _C =5mA, f=500MHz)	2200*	0.85	C _{res} 12pS	138C				
" 2473	"	RF	"	30	3	50	300	125	0.5	24	>20	10	5	10	-5	G _{re} = 15dB, N _F < 5 dB (V _{CE} =10V, I _C =7mA, f=200MHz)	2200*	C _{re} 0.5	C _{res} 12pS	138C				
" 2474	日電	SW	"	60	6	200	600	150	0.1	30	150	1	10			I _{on} < 70nS, t _{off} < 250nS t _{stg} < 200nS				138D				
" 2475	"	"	"	60	5	600	600	150	0.01	50	200	10	150			I _{on} < 35nS, t _{off} < 285nS t _{stg} < 225nS				138D				
" 2476	"	"	"	30		200	600	150	0.05	20	150	1	2			I _{on} < 70nS, t _{off} < 250nS t _{stg} < 200nS				138D				
" 2477	"	"	"	60	6	600	600	150	0.1	35	150	1	150			I _{on} < 35nS, t _{off} < 300nS t _{stg} < 225nS				138D				
" 2478																								
" 2479																								
" 2480	松下	RF.Osc.Mix	Si.EP	30	3	50	100	125			>25	10	2	10	-2	G _{re} = 20dB (f=100MHz)	1200*	C _{re} 1		176				
" 2481	東芝	PA	Si.E	150	6	1.5A	20W (T _c =25°C)	150	1	150	60~320	5	200	5	-200			>20*	13	20	342	2SA1021 とコンパリ		
" 2482	"	AF.RF	Si.T	300	7	100	900	150	1	240	30~150	10	20	10	-20			>50*	3		241			
" 2483	"	PA	Si.E	160	6	1.5A	15W (T _c =25°C)	175	1	150	100~320	5	200	5	-200			120*	<20	20	178			
" 2484	松下	"	Si.TP	80	5	5A	60W (T _c =25°C)	150	50	80	90	5	1A	5	-500			20*	100	10	152			
" 2485	"	"	"	100	5	6A	70W (T _c =25°C)	150	50	100	90	5	1A	5	-500			20*	140	10	152			
" 2486	"	"	"	120	5	7A	80W (T _c =25°C)	150	50	120	90	5	1A	5	-500			20*	190	10	152			
* " 2487	"	"	Si.Eme	150	5	6A	80W (T _c =25°C)	150			40~280	5	1A	10	-500			50*			102	2SA1063 とコンパリ		
" 2488	"	"	"	150	5	8A	100W (T _c =25°C)	150			40~280	5	1A	10	-500			50*			102	2SA1064 とコンパリ		
" 2489	"	"	"	150	5	10A	120W (T _c =25°C)	150			40~280	5	1A	10	-500			50*			102	2SA1065 とコンパリ		
" 2490	富士通	"	Si.EP	55	3.5	10A	90W (T _c =25°C)	175	1.6mA	20	50	5	6A			P _o = 75W, η _c = 65% (f=770MHz, V _{CE} =28V, P _i =25W)		48		168				
" 2491	サンケン	PA.SW	Si.Eme	100	15	6A	50W (T _c =25°C)	150	100	100	600	4	1A	12	-500			30*	200	15	298			
" 2492	"	PA	Si.EP	120	5	10A	100W (T _c =25°C)	150	100	120	60	4	3A	12	-500			70*	100	60	102			
" 2493	"	"	"	150	5	10A	100W (T _c =25°C)	150	100	150	60	4	3A	12	-500			70*	100	60	102			
" 2494	日電	"	Si.E	25	2	750	8.75W (T _c =25°C)	200	100	20	60	7	100			P _o = 14W (f=500MHz, V _{CE} =7.2V, P _i =125mW)		C _{re} 4		326				
" 2495	"	"	"	25	2	1.5A	17.5W (T _c =25°C)	200	100	20	60	7	200			P _o = 4W (f=500MHz, V _{CE} =7.2V, P _i =900mW)		C _{re} 8		326				
" 2496																								
" 2497	松下	RF	Si.EP	70	5	2A	1.2W	150	10	20	120	5	1A	5	-500			150*	35	110	222			
" 2498																								
" 2499																								
" 2500	東芝	SW.PA	Si.E	30	6	2A	900	150	0.1	30	140~600	1	500	1	-500			150*	27		241			
" 2501	新電元	SW	Si.T	500	7	3A	40W (T _c =25°C)	150	100	500	20	2	1.5A	10	-300			I _{on} < 1 μS, I _{stg} < 3 μS	t _f < 0.7 μS	20*		268	T3V40F1	